

## FEATURES

- PSRR: 100 dB minimum**
- CMRR: 105 dB typical**
- Very low supply current: 11  $\mu$ A maximum**
- 1.8 V to 5 V single-supply or  $\pm 0.9$  V to  $\pm 2.5$  V dual-supply operation**
- Rail-to-rail input and output**
- 3 mV offset voltage maximum**
- Very low input bias current: 0.5 pA typical**

## APPLICATIONS

- Pressure and position sensors**
- Remote security**
- Medical monitors**
- Battery-powered consumer equipment**
- Hazard detectors**

## GENERAL DESCRIPTION

The ADA4505-1 is single micropower amplifiers featuring rail-to-rail input and output swings while operating from a single 1.8 V to 5 V power supply or from dual  $\pm 0.9$  V to  $\pm 2.5$  V power supplies.

Employing a new circuit technology, these low cost amplifiers offer zero input crossover distortion (excellent PSRR and CMRR performance) and very low bias current, while operating with a supply current of less than 11  $\mu$ A per amplifier.

This combination of features makes the ADA4505-1 amplifier ideal choices for battery-powered applications because they minimize errors due to power supply voltage variations over the lifetime of the battery, and maintain high CMRR even for a rail-to-rail op amp.

## PIN CONFIGURATIONS

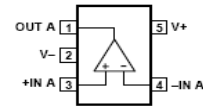
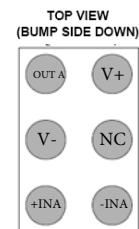


Figure 1. 5-Lead SOT23 (RJ-5)



NC = No Connect

Figure 2. 6-Ball WLCSP (CB-6-2)

Remote battery-powered sensors, handheld instrumentation and consumer equipment, hazard detectors (for example, smoke, fire, and gas), and patient monitors can benefit from the features of the ADA4505-1 amplifiers.

The ADA4505-1 is specified for both the industrial temperature range ( $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ) and the extended industrial temperature range ( $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ). The ADA4505-1 single amplifier is available in standard 5-lead SOT23 and 6-ball WLCSP packages.

The ADA4505-1 is members of a growing series of zero crossover op amps offered by Analog Devices, Inc., including the AD8506/AD8508/ADA4505-2/ADA4505-4, which also operate from a single 1.8 V to 5 V power supply or from dual  $\pm 0.9$  V to  $\pm 2.5$  V power supplies.

### Rev. PrA

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

## SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS—5 V OPERATION

$V_{SY} = 5\text{ V}$ ,  $V_{CM} = V_{SY}/2$ ,  $T_A = 25^\circ\text{C}$ ,  $R_L = 100\text{ k}\Omega$  to GND, unless otherwise specified.

Table 1.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	$V_{OS}$	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	3	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2	pA
					50	pA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.05	1	pA
					25	pA
					130	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		5	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	90	105		dB
			90			dB
			85			dB
Large Signal Voltage Gain	$A_{VO}$	$0.05\text{ V} \leq V_{OUT} \leq 4.95\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	105	120		dB
			100			dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2		$\mu\text{V}/^\circ\text{C}$
Input Resistance	$R_{IN}$			220		G $\Omega$
Input Capacitance Differential Mode	$C_{INDM}$			2.5		pF
Input Capacitance Common Mode	$C_{INCM}$			4.7		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$R_L = 100\text{ k}\Omega$ to GND $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	4.98	4.99		V
			4.98			V
			4.9	4.95		V
			4.9			V
Output Voltage Low	$V_{OL}$	$R_L = 100\text{ k}\Omega$ to $V_{SY}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2	5	mV
					5	mV
				10	25	mV
					25	mV
Short-Circuit Limit	$I_{SC}$	$V_{OUT} = V_{SY}$ or GND		$\pm 40$		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to $5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	100	110		dB
			100			dB
			95			dB
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		7	11	$\mu\text{A}$
					15	$\mu\text{A}$
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		6		mV/ $\mu\text{s}$
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		50		kHz
Phase Margin	$\Phi_M$	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		52		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n$ p-p	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		2.95		$\mu\text{V}$ p-p
Voltage Noise Density	$e_n$	$f = 1\text{ kHz}$		65		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1\text{ kHz}$		20		fA/ $\sqrt{\text{Hz}}$

**ELECTRICAL CHARACTERISTICS—1.8 V OPERATION**

$V_{SY} = 1.8\text{ V}$ ,  $V_{CM} = V_{SY}/2$ ,  $T_A = 25^\circ\text{C}$ ,  $R_L = 100\text{ k}\Omega$  to GND, unless otherwise specified.

**Table 2.**

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
<b>INPUT CHARACTERISTICS</b>						
Offset Voltage	$V_{OS}$	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	3	mV
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.5	2	pA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.05	1	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		1.8	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	85	100		dB
Large Signal Voltage Gain	$A_{VO}$	$0.05\text{ V} \leq V_{OUT} \leq 1.75\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	80	115		dB
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2.5		$\mu\text{V}/^\circ\text{C}$
Input Resistance	$R_{IN}$			220		G $\Omega$
Input Capacitance Differential Mode	$C_{INDM}$			2.5		pF
Input Capacitance Common Mode	$C_{INCM}$			4.7		pF
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage High	$V_{OH}$	$R_L = 100\text{ k}\Omega$ to GND $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.78	1.79		V
		$R_L = 10\text{ k}\Omega$ to GND $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.78	1.75		V
Output Voltage Low	$V_{OL}$	$R_L = 100\text{ k}\Omega$ to $V_{SY}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2	5	mV
		$R_L = 10\text{ k}\Omega$ to $V_{SY}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		12	25	mV
Short-Circuit Limit	$I_{SC}$	$V_{OUT} = V_{SY}$ or GND		$\pm 3.8$		mA
<b>POWER SUPPLY</b>						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 1.8\text{ V}$ to $5\text{ V}$ $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	100	110		dB
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	95	7	11	$\mu\text{A}$
<b>DYNAMIC PERFORMANCE</b>						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		6.5		mV/ $\mu\text{s}$
Gain Bandwidth Product	GBP	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		50		kHz
Phase Margin	$\Phi_M$	$R_L = 1\text{ M}\Omega$ , $C_L = 20\text{ pF}$ , $G = 1$		52		Degrees
<b>NOISE PERFORMANCE</b>						
Voltage Noise	$e_n$ p-p	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		2.95		$\mu\text{V}$ p-p
Voltage Noise Density	$e_n$	$f = 1\text{ kHz}$		65		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1\text{ kHz}$		20		fA/ $\sqrt{\text{Hz}}$

## ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	5.5 V
Input Voltage	$\pm V_{SY} \pm 0.1$ V
Input Current <sup>1</sup>	$\pm 10$ mA
Differential Input Voltage <sup>2</sup>	$\pm V_{SY}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-65°C to +150°C
Operating Temperature Range	-40°C to +125°C
Junction Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

<sup>1</sup> Input pins have clamp diodes to the supply pins. Input current should be limited to 10 mA or less whenever the input signal exceeds the power supply rail by 0.5 V.

<sup>2</sup> Differential input voltage is limited to 5 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. This was measured using a standard 2-layer board, unless otherwise specified.

Table 4. Thermal Resistance

Package Type	$\theta_{JA}$	$\theta_{JB}^1$	$\theta_{JC}$	Unit
5-Lead SOT23 (RJ-5)	TBD	TBD	TBD	°C/W
6-Ball WLCSP (CB-6-2)				
2-Layer PCB (1SOP)	TBD	TBD	N/A	°C/W
4-Layer PCB (2SOP)	TBD	TBD	N/A	°C/W

<sup>1</sup> Junction-to-board thermal resistance.

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.